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(71) Applicant (for all designated States except US): **SHOWA DENKO K.K.** [JP/JP]; 13-9, Shibadaimon 1-chome, Minato-ku, Tokyo 1058518 (JP).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **SAKURAI, Tetsuo** [JP/JP]; c/o Showa Denko K.K., 1-1, Ohnodai 1-chome, Midori-ku, Chiba-shi, Chiba 2670056 (JP).

(74) Agents: **AOKI, Atsushi** et al.; A. Aoki, Ishida & Associates, Toranomon 37 Mori Bldg., 5-1, Toranomon 3-chome, Minato-ku, Tokyo 1058423 (JP).

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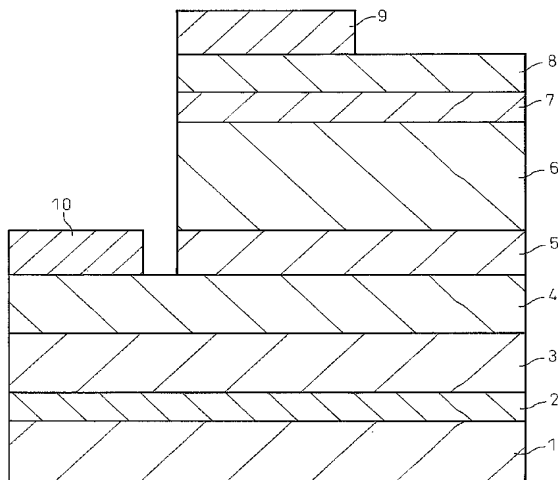
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(54) Title: GROUP III NITRIDE SEMICONDUCTOR DEVICE AND LIGHT-EMITTING DEVICE USING THE SAME



(57) Abstract: An object of the present invention is to provide a Group III nitride semiconductor device exhibiting improved crystallinity and a good performance. The inventive Group III nitride semiconductor device comprises a substrate, and a plurality of Group III nitride semiconductor layers provided on the substrate, wherein a first layer which is in contact with the substrate is composed of silicon-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$). Also, the inventive Group III nitride semiconductor device comprises a substrate, and a plurality of Group III nitride semiconductor layers provided on the substrate, wherein a first layer which is in contact with the substrate is composed of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$), and the difference in height between a protrusion and a depression which are present at the interface between the first layer and a second layer provided thereon is 10 nm or more and is equal to, or less than, 99% the thickness of the first layer.

WO 2005/062390 A1